

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet 2 of 2

Complete if Known

Application Number	TBA
Filing Date	Herewith
First Named Inventor	TAKEDA et al.
Group Art Unit	TBA
Examiner Name	TBA
Attorney Docket Number	KOJIM-448

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials *	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
S.T.L.	L	International Work Shop 157nm Lithography MIT-LL, Boston, MA, May 5, 1999	
	M	Kunz et al. "Outlook for 157 nm Resist Design," J. Vac. Sci. Technol. B 17(6), Nov/Dec 1999, pp. 3267-3272	
	N	Chiba et al., "157 nm Resist Materials: A Progress Report," J. Photopolymer Science and Technology, Vol. 13, No. 4 (2000) pp 657-664	
	O	Schmaljohann et al., "Fundamental Studies of Fluoropolymer Photoresists for 157 nm Lithography," J. of Photopolymer Science Technology, Vol., 13, No. 3 (2000) pp 451-458	
	P	Brunsvold et al., "Evaluation of a Deep UV Bilayer Resist for Sub-Half Micron Lithography," SPIE Vol. 1925 (1993), pp. 377-387	
	Q	Hatakeyama et al., "Investigation of Discrimination Enhancement in Polysilsesquioxane Based Positive Resist for ArF Lithography" SPIE Vol. 3333, pp. 62-72	
	R	Blakeney et al., "Evaluation of Materials for 193-nm Lithography" J of Photopolymer Science and Technology, Vol. 9, No. 3 (1996) pp 435-446	
	S	Kessel, et al., "novel Silicon-Containing Resists for EUV and 193 nm Lithography" SPIE Vol. 3678 (1999), pp. 214-220	
	T	Lin et al., "A High Resolution 248 nm Bilayer Resist" SPIE Vol. 3678 (1999) pp. 241250	
	U	Boardman et al., "Chemical Aspects of Silicon-Containing Bilayer Resists" SPIE Vol. 3678 (1999) pp. 562-572	
✓	V	Kim et al., "Chemically amplified resist based on the methacrylate polymer with 2-trimethylsilyl-2-propyl ester protecting group" SPIE Vol. 3678 (1999) pp 420-428	

Examiner
Signature

Li A. Lee

Date
Considered

9-25-03

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ² See attached Kinds of U.S. Patent Documents. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Assistant Commissioner for Patents, Washington, DC 20231